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U.S. UTILITY Patent Application

PATENT NUMBER and  
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU
10092795	03/06/2002	438		2813

EXAMINER  
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I. PHAM

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\*\*CONTINUING DATA VERIFIED: *TN*  
*None*

\*\* FOREIGN APPLICATIONS VERIFIED: *None*  
*TN*

PG-PUB DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☐ yes ☒ no  
35 USC 119 conditions met ☐ yes ☒ no  
Verified and Acknowledged Examiners's initials *TN*

ATTORNEY DOCKET NO

7017/ETCH/CORE

TITLE : Method of plasma etching of high-K dielectric materials with high selectivity to underlying layers  
U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)

<b>NOTICE OF ALLOWANCE MAILED</b>		<b>CLAIMS ALLOWED</b>	
		Assistant Examiner	
<b>ISSUE FEE</b>		Total Claims	
Amount Due	Date Paid	Print Claim for 0.6	
		<b>DRAWING</b>	
		Sheet One	Page One
		Sheet Two	Page Two
		Application Examiner	
<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>		<b>PREPARED FOR ISSUE</b>	
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